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Introduction

Welcome to the 2009 Lithography Asia conference held in Taipei, Taiwan. This is the second year in a row that we have held a general conference on lithographic science and technology in Asia. This conference demonstrated the continuing increase in research and development activities in lithography in Asia. We are very pleased to have been the chairs of this conference, and in this volume you will find papers describing some very exciting developments in many fields.

2009 was not the best year for the economy. With great uncertainty in world markets, there is no doubt that times are troubled; although, a sign of recovery appears toward the end of the year. In spite of that, we were very pleased to see a fairly robust attendance for this year. This demonstrates an industry wide willingness to continue to pursue research, creativity, and innovation to address manufacturing problems, and it gives great hope for the future of these promising technologies.

We have seen promising development not only in the EUV Lithography but also in parallel e-beam technology. Also, outstanding work was presented on the double patterning/process technology as well as on the source mask optimization to extend the life of water immersion ArF lithography. Of course, we received significant numbers of paper on the continual innovative work on process control including related metrology technology, mask fabrication and especially on lithographic material and process advancement.

We are very impressed by the strength and diversity of the work presented here; we hope you are as well. Of course, this would not be possible without the help of the conference Program Committee, and the SPIE staff. We thank them especially for their contributions in making this conference a success.

Alek C. Chen
Woo-Sung Han
Burn J. Lin
Anthony Yen

